

TECHNICAL DATA DATA SHEET 5518, REV -

HERMETIC POWER MOSFET N-CHANNEL

FEATURES:

- 90 Volt, 3.6 Ohm low capacitance MOSFET
- Hermetically Sealed TO-205/TO-39 package
- S-100 screening available 2N6661S
- Low input and Output Leakage

MAXIMUM RATINGS

ALL RATINGS ARE AT $T_{_{\Delta}}$ = 25°C UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
DRAIN TO SOURCE VOLTAGE	V_{DS}	90	-	-	Volts
GATE TO SOURCE VOLTAGE	V_{GS}	-	-	± 20	Volts
CONTINUOUS DRAIN CURRENT V _{GS} =10V, T _C = 25°C	I _D	-	-	0.86	Amps
$V_{GS}=10V, T_{C}=100^{\circ}C$				0.54	
PULSED DRAIN CURRENT @ T _C = 25°C	I _{DM}	-	-	3	Amps
OPERATING AND STORAGE TEMPERATURE	T_{OP}/T_{STG}	-55	-	150	°C
TERMAL RESISTANCE JUNCTION TO CASE	$R_{\theta JC}$	-	-	20	°C/W
TOTAL DEVICE DISSIPATION @ T _C = 25°C	P _D	-	-	6.25	Watts

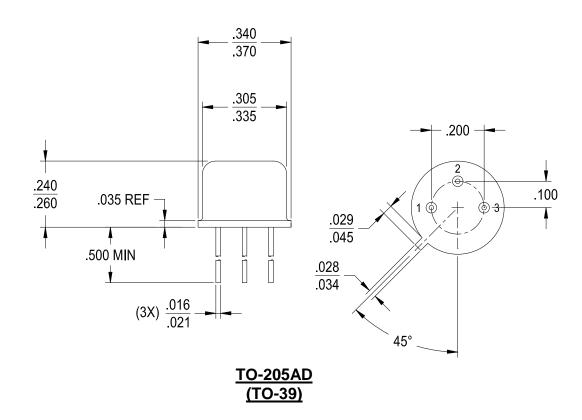
ELECTRICAL CHARACTERISTICS

DRAIN TO SOURCE BREAKDOWN VOLTAGE		BV _{DSS}	90	125	-	Volts
$V_{GS} = 0V, I$	_D = 10µA					
DRAIN TO SOURCE ON STATE RESISTANCE						Ω
$V_{GS} = 5V$,		$R_{DS(ON)}$	-	3.8	5.3	
$V_{GS} = 10V$	$I_{D} = 1A$		-	3.6	4.4	
$V_{GS} = 10V, I_{D} = 1A, T_{J}$	= 125°C		-	6.7	7.5	
GATE THRESHOLD VOLTAGE $V_{DS} = V_{GS}$, I	$_{D} = 1 mA$	$V_{GS(th)}$	0.8	1.6	2.0	Volts
$V_{DS} = V_{GS}, I_{D} = 1 \text{mA}, T_{J} = 125 ^{\circ}\text{C}$			0.3	1.3	-	
$V_{DS} = V_{GS}, I_{D} = 1 \text{mA}, T_{J} = -55 ^{\circ}\text{C}$			-	1.8	2.5	
FORWARD TRANSCONDUCTANCE		g_{fs}	-	0.34		S(1/Ω)
$V_{DS} = 7.5V, I_{DS}$	s = 0.475A					` ,
ZERO GATE VOLTAGE DRAIN CURRENT			-	-		μΑ
$V_{DS} = 72V, V_{GS} = 0V$		I_{DSS}			1	
$V_{DS} = 72V, V_{GS} = 0V, T_{SS}$					100	
GATE TO SOURCE LEAKAGE FORWARD @ F	REVERSE	I_{GSS}	-	-		nA
$V_{GS} = \pm 20V$					±100	
$V_{GS} = \pm 20V, T_{J} =$	125°C				±500	
TURN ON TIME $V_{DD} = 25V$, Y	$V_{GS} = 10V$	$t_{(ON)}$	-	6	10	nsec
TURN OFF TIME $I_D = 1A, R_G$	= 23Ω	t _(OFF)		8	10	
DIODE FORWARD VOLTAGE $T_J = 25^{\circ}C$, I	s = 0.86A,	V_{SD}	0.7	0.9	1.4	Volts
	$V_{GS} = 0V$					
	$I_{GS} = 0 \text{ V}$	C_{iss}	-	35	-	pF
	$I_{DS} = 25 \text{ V}$	C_{oss}		15		
REVERSE TRANSFER CAPACITANCE f	= 1 MHz	C_{rss}		2		



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MECHANICAL DIMENSIONS: in Inches / mm



PINOUT TABLE

DEVICE TYPE	PIN 1	PIN 2	PIN 3
MOSFET TO-205 (TO-39) PACKAGE	SOURCE	GATE	DRAIN

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